Complementary Silicon Plastic Power Transistors

These devices are designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD243B, BD244B BD243C, BD244C	V _{CEO}	80 100	Vdc
Collector–Base Voltage BD243B, BD244B BD243C, BD244C	V _{CB}	80 100	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	Ι _C	6	Adc
Collector Current – Peak	I _{CM}	10	Adc
Base Current	Ι _Β	2.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	65 0.52	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

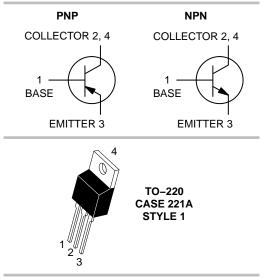
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.92	°C/W



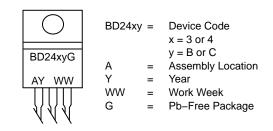
ON Semiconductor®

http://onsemi.com

6 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 80–100 VOLTS 65 WATTS



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
BD243BG	TO-220 (Pb-Free)	50 Units / Rail
BD243CG	TO–220 (Pb–Free)	50 Units / Rail
BD244BG	TO–220 (Pb–Free)	50 Units / Rail
BD244CG	TO-220 (Pb-Free)	50 Units / Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 30 \text{ mAdc}, I_B = 0$) BD243B, BD244B BD243C, BD244C	V _{CEO(sus)}	80 100		Vdc
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ BD243B, BD243C, BD244B, BD244C	I _{CEO}	_	0.7	mAdc
Collector Cutoff Current $(V_{CE} = 80 \text{ Vdc}, V_{EB} = 0)$ BD243B, BD244B $(V_{CE} = 100 \text{ Vdc}, V_{EB} = 0)$ BD243C, BD244C	ICES	-	400 400	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS (Note 1)		•	•	•
DC Current Gain (I _C = 0.3 Adc, V _{CE} = 4.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)	h _{FE}	30 15		-
Collector–Emitter Saturation Voltage $(I_{C} = 6.0 \text{ Adc}, I_{B} = 1.0 \text{ Adc})$	V _{CE(sat)}	_	1.5	Vdc
Base–Emitter On Voltage ($I_C = 6.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)	V _{BE(on)}	_	2.0	Vdc
DYNAMIC CHARACTERISTICS	÷.			•
Current–Gain – Bandwidth Product (Note 2) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$)	f _T	3.0	_	MHz
Small–Signal Current Gain ($I_C = 0.5 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	h _{fe}	20	-	-

1. Pulse Test: Pulsewidth \leq 300 µs, Duty Cycle \leq 2.0%. 2. f_T = h_{fe} • f_{test}

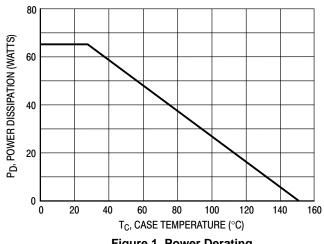


Figure 1. Power Derating

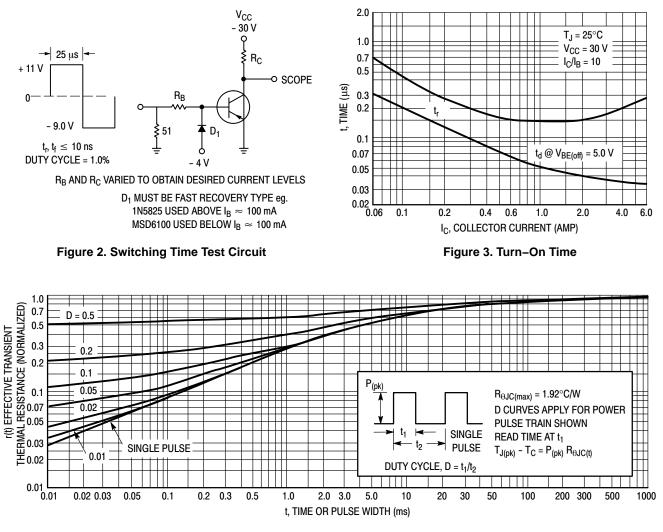


Figure 4. Thermal Response

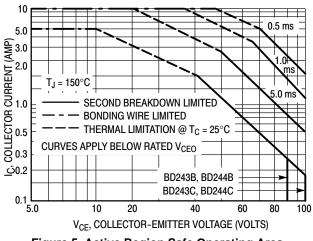
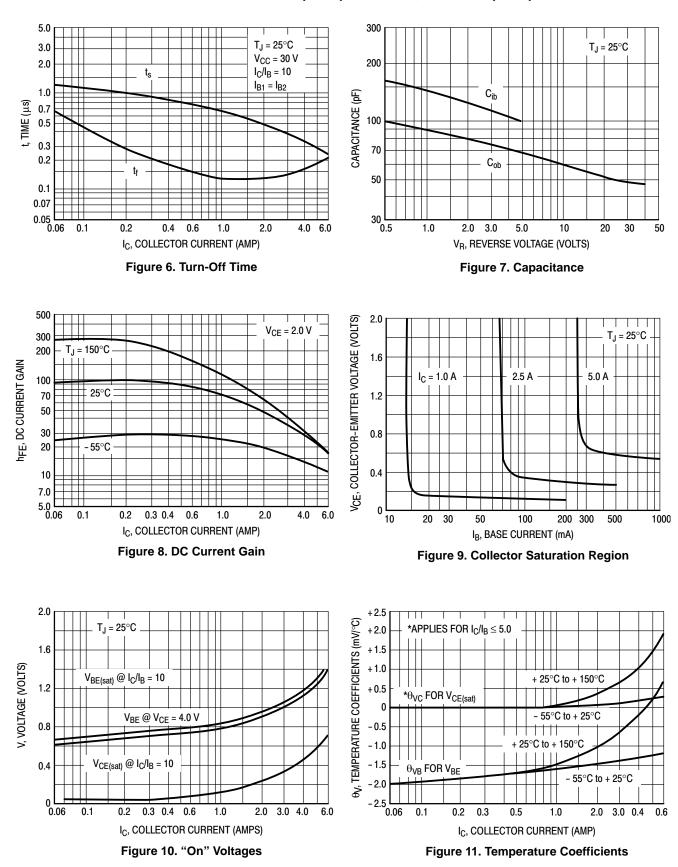
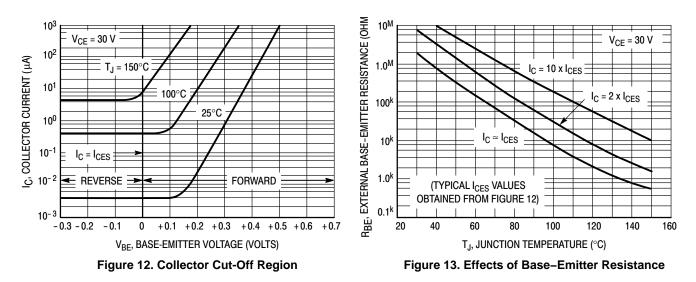


Figure 5. Active Region Safe Operating Area

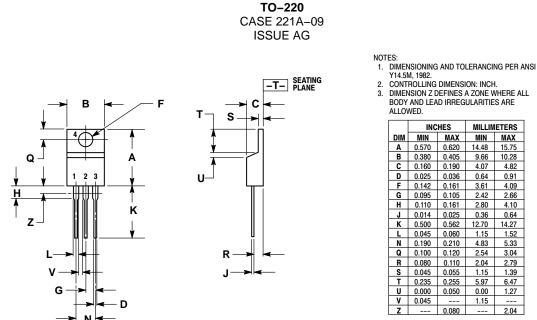
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$: T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





PACKAGE DIMENSIONS



INCHES MILLIMETERS MIN MAX MIN MAX A 0.570 0.620 14.48 15.75 0.405 0.380 9.66 10.28 0.160 4.07 4.82 D 0.025 0.036 0.64 0.91 0.142 0.161 3.61 4.09 **G** 0.095 0.105 2.42 2.66 H 0.110 0.161 2.80 4.10 **J** 0.014 0.025 0.36 0.64 K 0.500 0.562 12.70 14.27 L 0.045 N 0.190 0.060 1.15 1.52 0.210 4.83 5.33 **Q** 0.100 0.120 2.54 3.04 0.110 0.080 2.04 2.79 S 0.045 T 0.235 0.055 1.15 1.39 0.255 5.97 6.47 0.000 0.050 0.00 1.27 V 0.045 1.15 0.080 2.04

STYLE 1: PIN 1. BASE

2. COLLECTOR 3.

EMITTER COLLECTOR 4

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